

Modal and Thermal Characteristics of 670nm VCSELs

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Vixar

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Overview

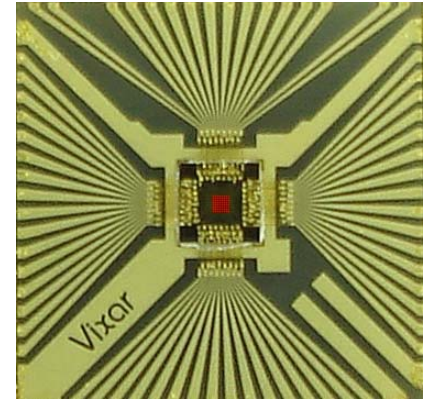
- Applications of red VCSELs
- Device performance / limitations
- Thermal management
- Improved oxide VCSEL mode control
- Results / Performance Data
- Summary

Who Is Vixar?

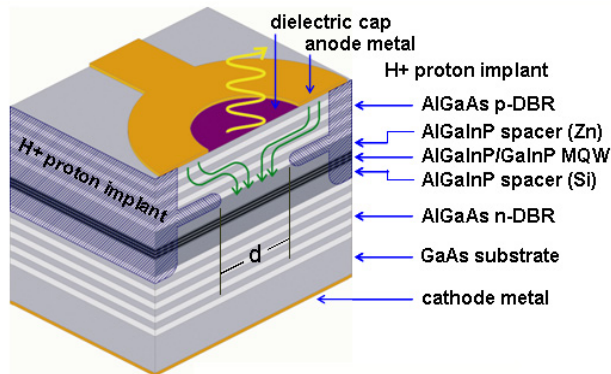
- Vixar founded in late 2004 (Maple Grove, Minnesota)
 - Focused on 660nm-800nm VCSELs
 - Biomedical, industrial, commercial and military sensors
 - Founding team has an extensive history in VCSEL R&D and productization
 - Outsource Model: “Fabless Opto”

Applications/Value Propositions

- **Laser Printing**
 - 2D arrays for speed enhancement
 - Preferred wavelength for photosensitive materials
- **Oximetry/BioSensors**
 - Low power for wireless sensors
 - High yields to wavelength specs; Low $d\lambda/dT$
- **Industrial Sensors**
 - Superior beam characteristics compared to LEDs
 - Reduced cost of optics and increased mechanical robustness
 - Arrays can eliminate mechanical scanning
- **Residential/Consumer POF**
 - High speed (>2Gb/sec) modulation
 - Low NA for efficient fiber coupling
- **Spectroscopy**
 - Narrow linewidth, polarization stable
- **Medical Diagnostics and Imaging**
 - Large scale linear arrays
- **MEMS Integration (beam scanners)**
 - Vertical emission simplifies packaging



Typical Device Structure



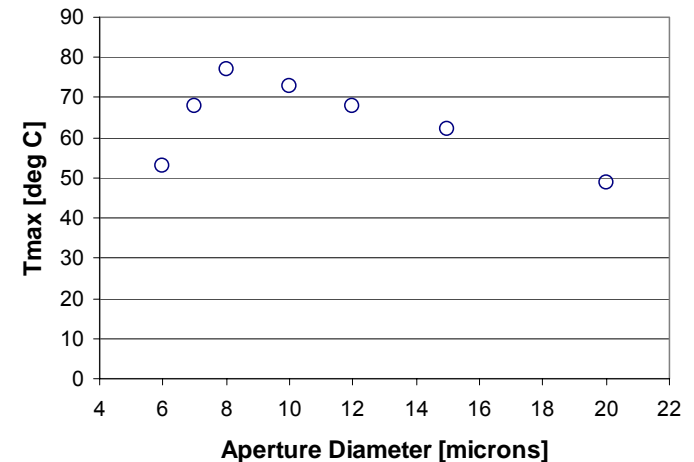
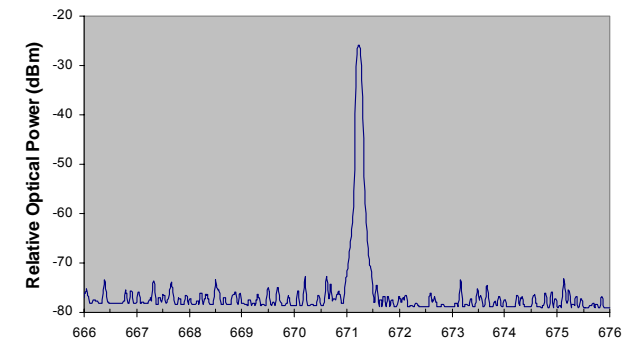
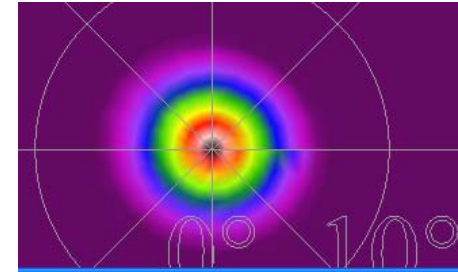
- $\text{Al}_{0.5}\text{Ga}_{0.5}\text{As} / \text{Al}_x\text{Ga}_{(1-x)}\text{As}$ DBRs: $x > 0.92$
- $1-3\lambda$ cavity
- GaInP QW's (compressive strain)
- Tensile strained barriers and spacer transition
- 50% → 70% graded AlGaInP SCH
- Zn doping in p-spacer
- Misoriented substrates

Well Known Technical Challenges

- Small conduction band offset AlGaInP
 - Thermal carrier overflow at high J, T
- Need for ~50% AlGaAs in DBRs
 - Poor thermal conductivity (high thermal impedance)
 - Low index contrast DBR (resistance, thermal impedance)
 - Reduced mobility (increased resistance)
- Zn diffusion in active region
 - Burn-in effects
 - Reliability concerns
- Oxygen Incorporation
 - Reduction in radiative efficiency

Demonstrated CW Performance (Proton)

- Single-mode
 - 2.8mW @ 671nm: 4.5mA, 20C
 - Divergence = 5.5 to 7.5 deg FWHM
 - SMSR > 45dB
- Multi-mode
 - 11.5mW @ 673nm, 20C
 - Peak WPE of 19.9% at 18mA.
- Temperature
 - 670nm Lasing to 79C
 - >1mW @ 60C
- Efficiency
 - Peak WPE 22.9%
- Polarization stability
 - PER 20-25dB typical



Proton VCSEL Limitations

For many applications, proton performance is fine
Good single-mode power
Adequate temperature performance

But...

Proton VCSELs don't modulate very well
Severe DCD for low duty cycle, high ER applications
Thermal lensing

Example: Laser Printing

Desire >20db (i.e. infinite) extinction ratio
Minimal turn-on delay
5-10ns pulse widths
Low duty cycles ($\ll 1\%$)

The Oxide Alternative

Red oxide VCSELs modulate well

But...

Low single-mode power

Exhibit poorer temp performance

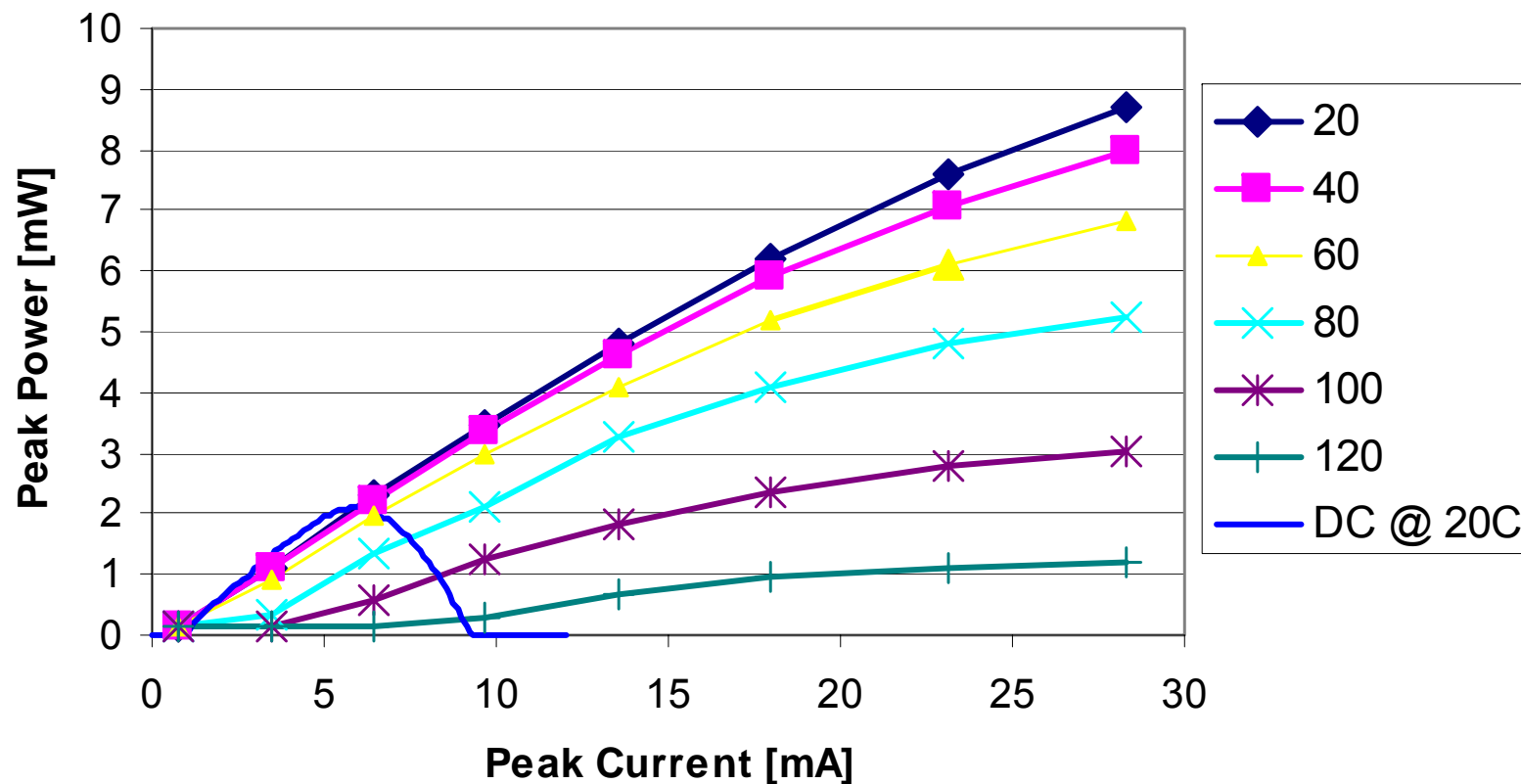
Goal: Improve red oxide VCSEL performance through

- 1) Improved thermal management
- 2) Improved mode control

High Temp Pulsed Operation

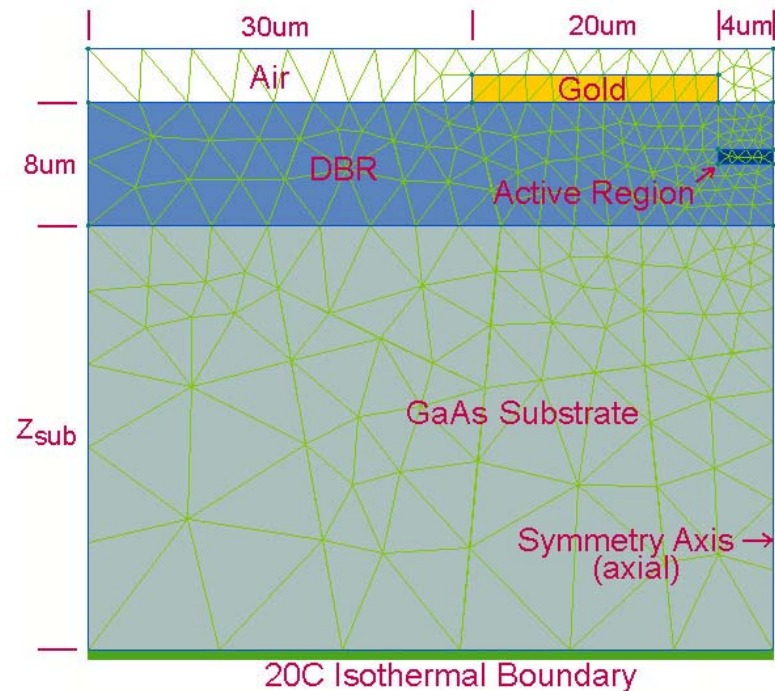
Performance under pulsed conditions

50nS Pulse; 1% Duty



Thermal Model

- Planar and etched mesa device structures
- Extraction of thermal impedance

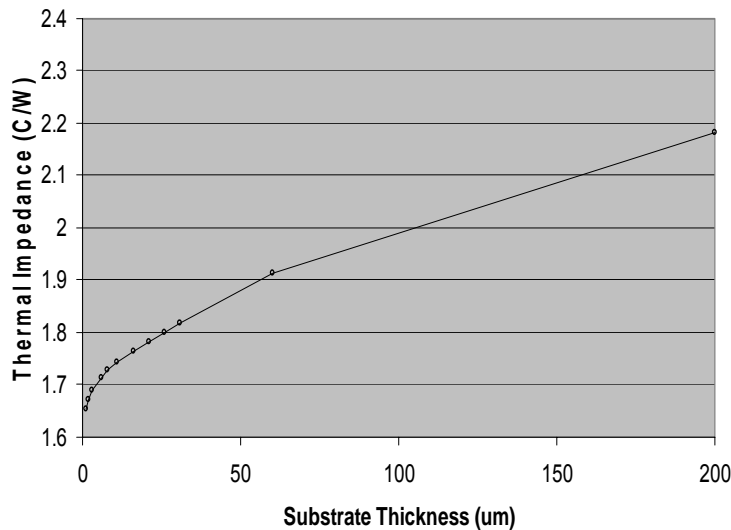


Anisotropic DBR thermal conductivity

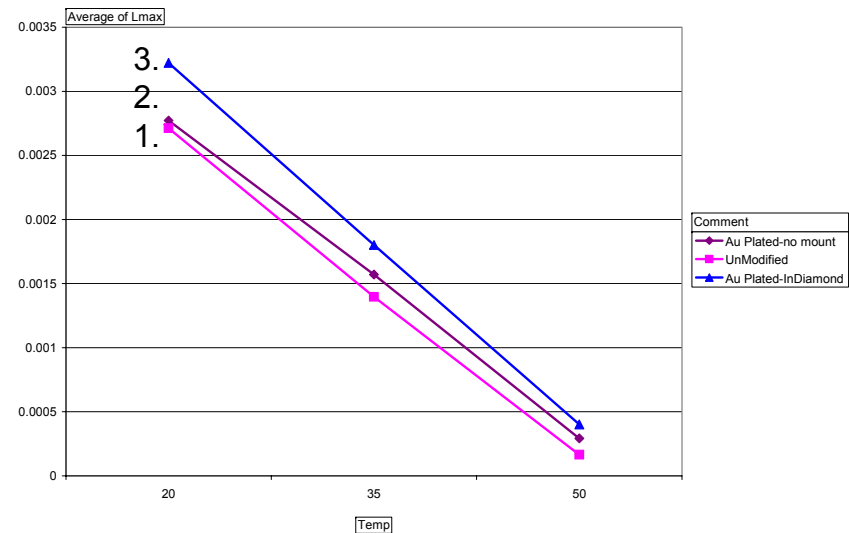
$$K_r = (K_{\text{AlAs}} + K_{\text{AlGaAs}})/2 = (90 + 10)/2 = 50 \text{ W/mK}$$
$$K_z = 2 / (1/K_{\text{AlAs}} + 1/K_{\text{AlGaAs}}) = 2 / (1/90 + 1/10) = 18 \text{ W/mK}$$

Substrate Removal

- Common practice in HB LEDs



Rth vs. Substrate Thickness
(modeled)



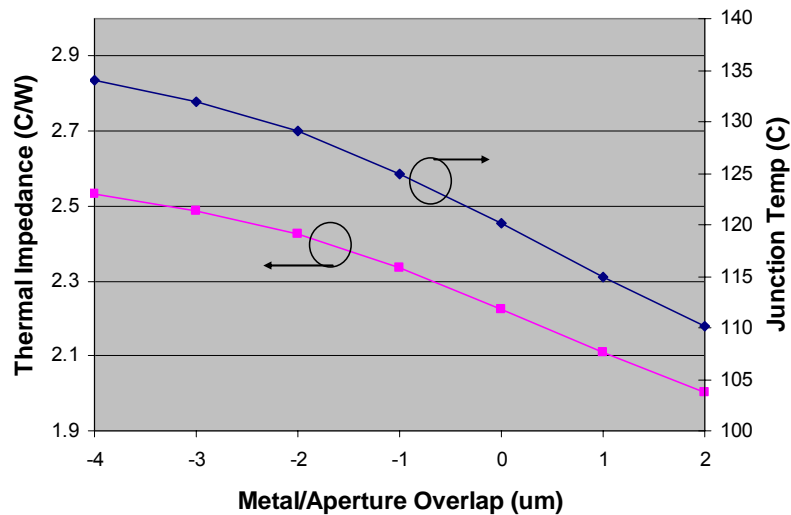
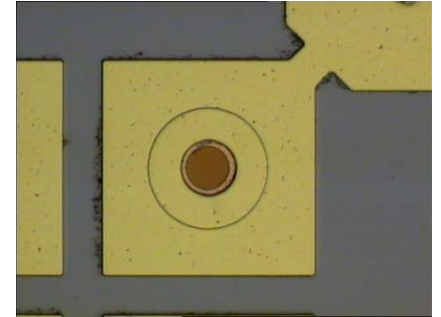
Lmax vs. Temp
(experimental)

- Not terribly effective for red VCSELs
- ~10% reduction in Rth reasonable
- Not attractive for processing

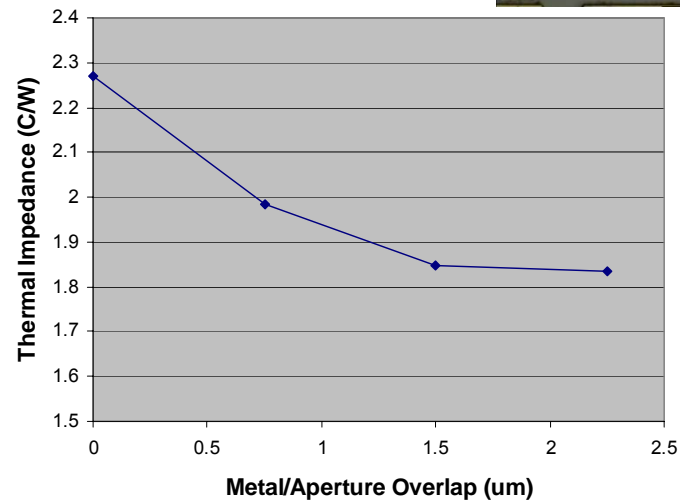
- Substrate removed
- Au plated
- Diamond fused

Aperture/Metal Overlap

- Strong effect on R_{th}



(modeled)

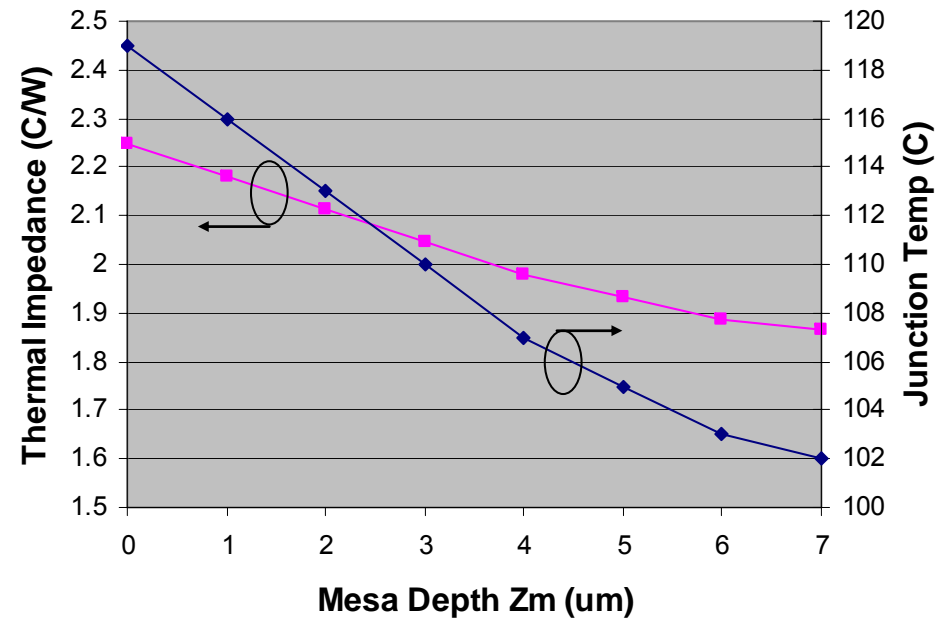
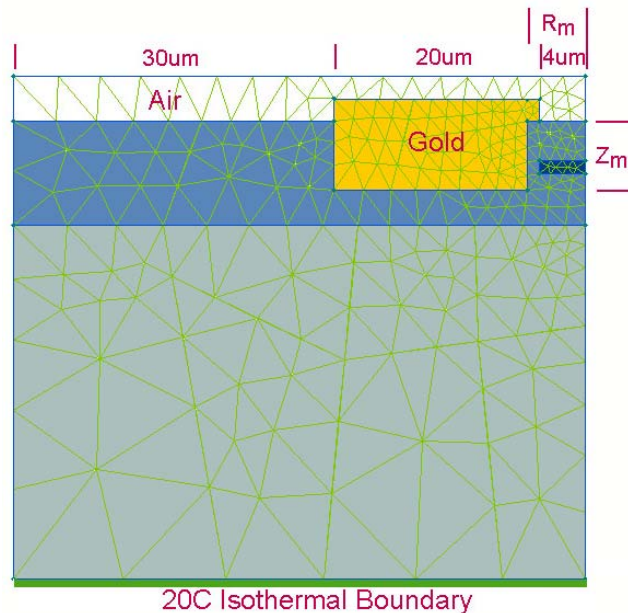


(experimental)

- Penalty in output power due to vignetting
- Alignment-related uniformity variation

Lateral Mesa Heatsinking

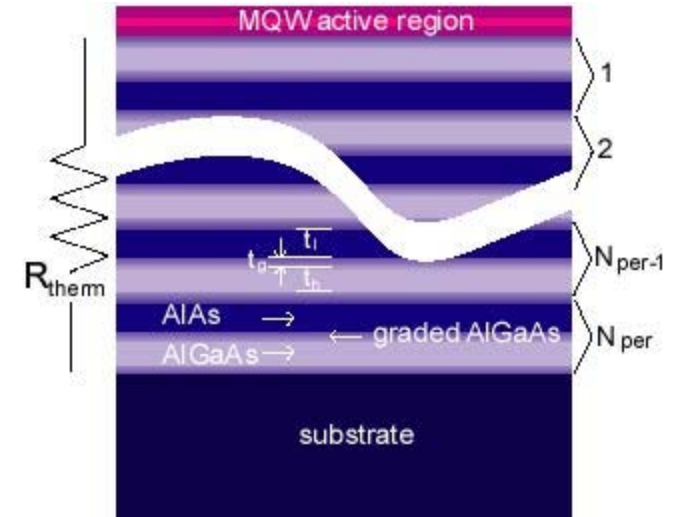
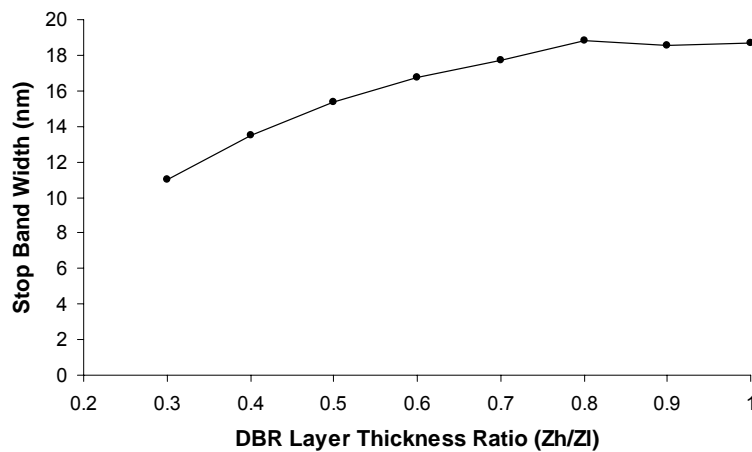
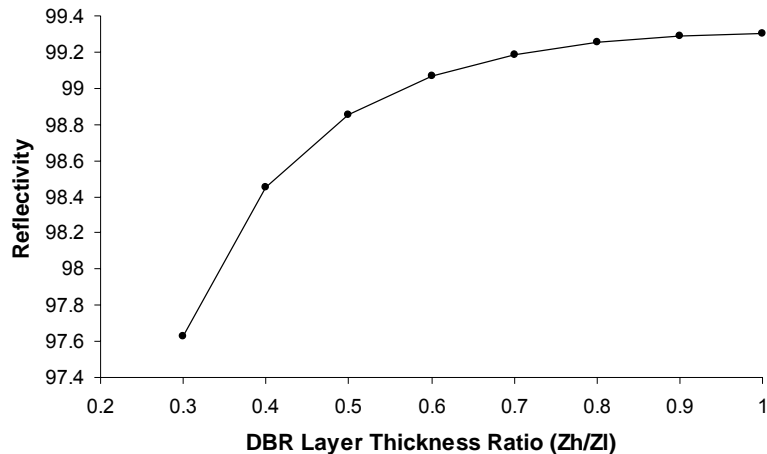
- Mesa etch with metal plating



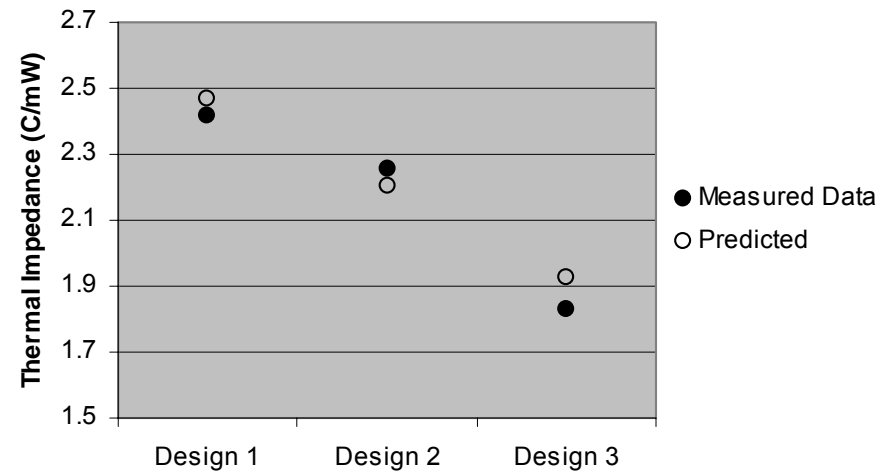
- Potentially effective (~15% reduction in R_{th})
- Increased process complexity
- Demonstration in process @CSU (Lear)

Improved Mirror Design

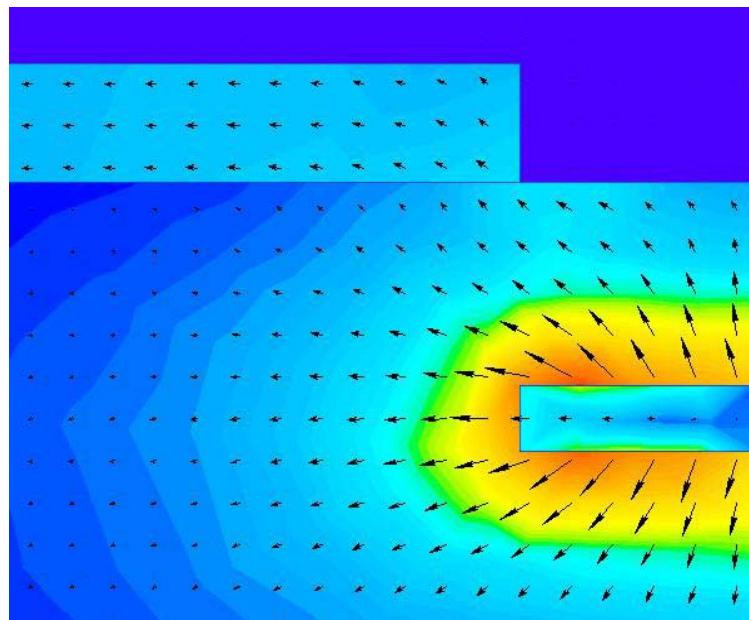
- Depart from quarter wave stack
- ~30% reduction in R_{th}
- Minimal observable increase in I_{th}



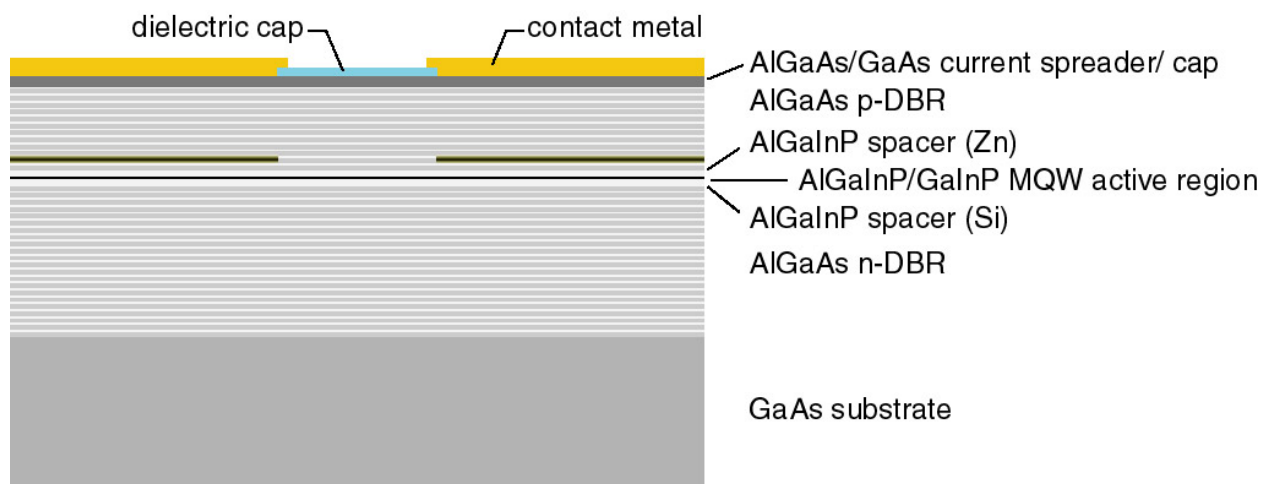
Design	Zh/Zl	Grade
1	0.90	12nm
2	0.88	20nm
3	0.58	12nm



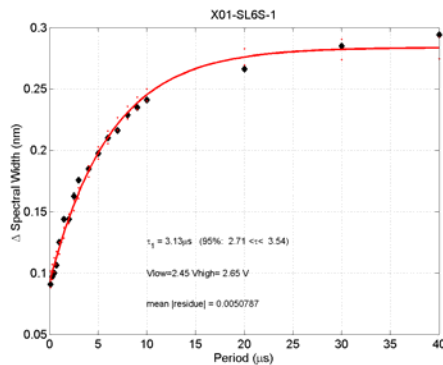
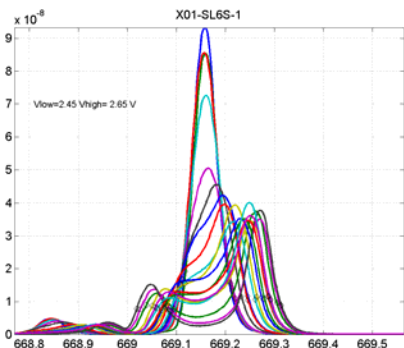
Junction Heating



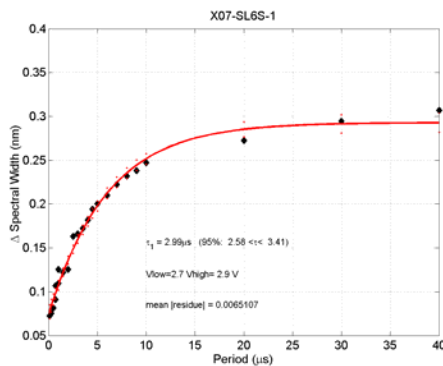
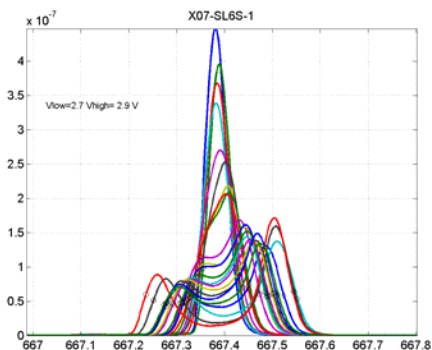
Color map of heat flux



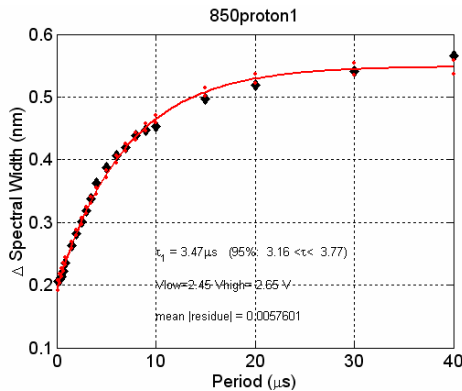
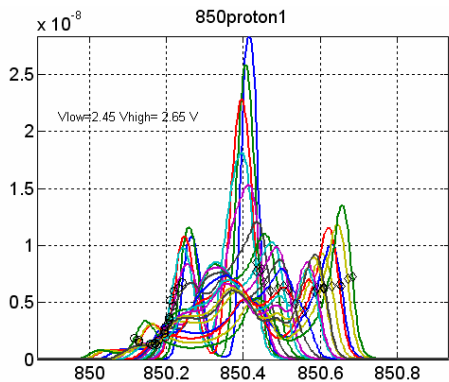
Junction Heating Time Constant



1λ AIAs Cavity: $\tau=3.13\mu\text{S}$



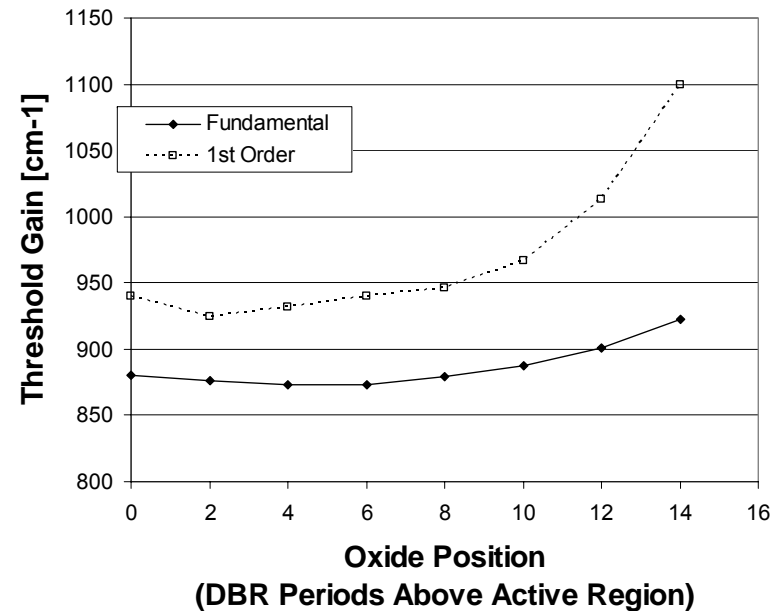
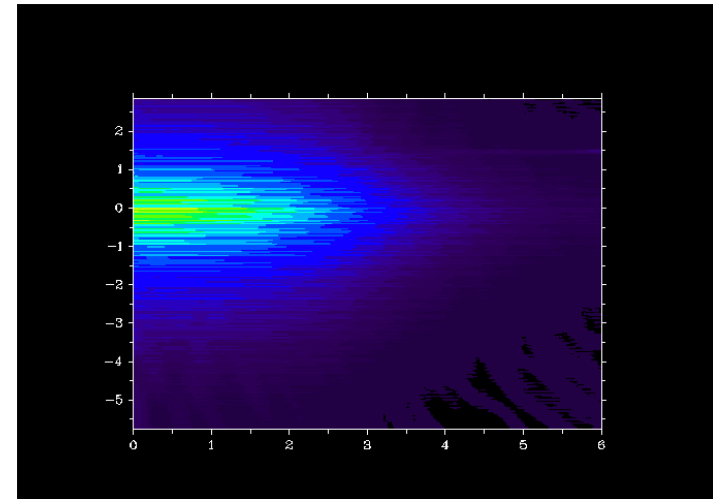
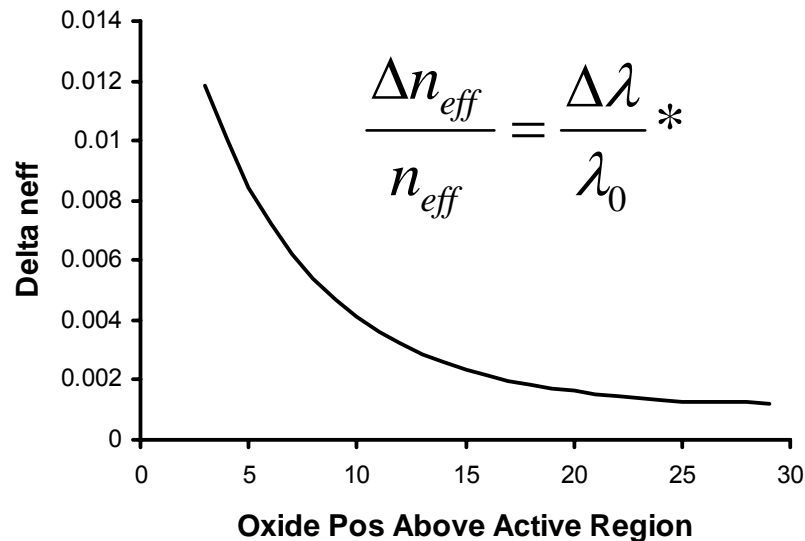
2λ AIAs Cavity: $\tau=2.99\mu\text{S}$



850nm: $\tau=3.47\mu\text{S}$

Oxide VCSEL Mode Control

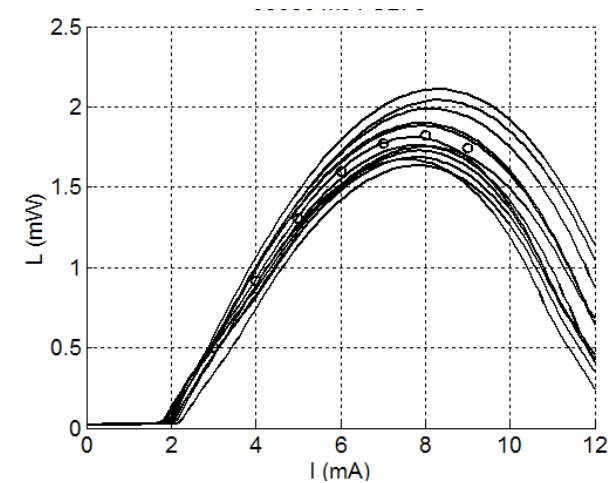
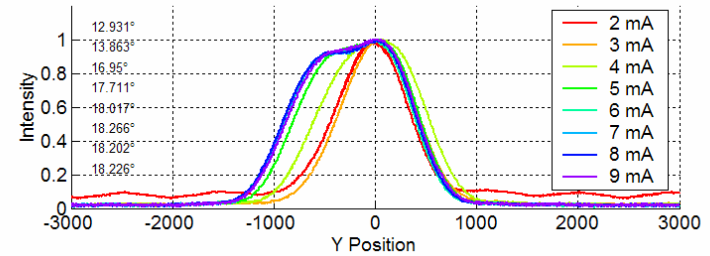
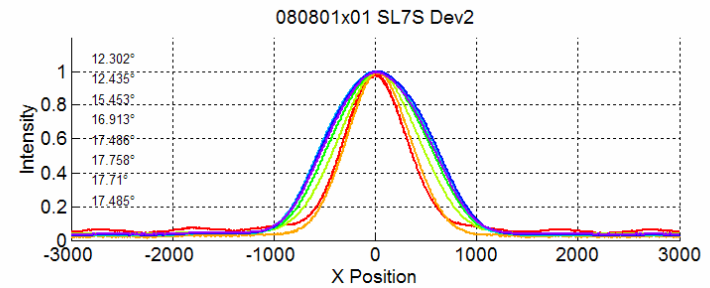
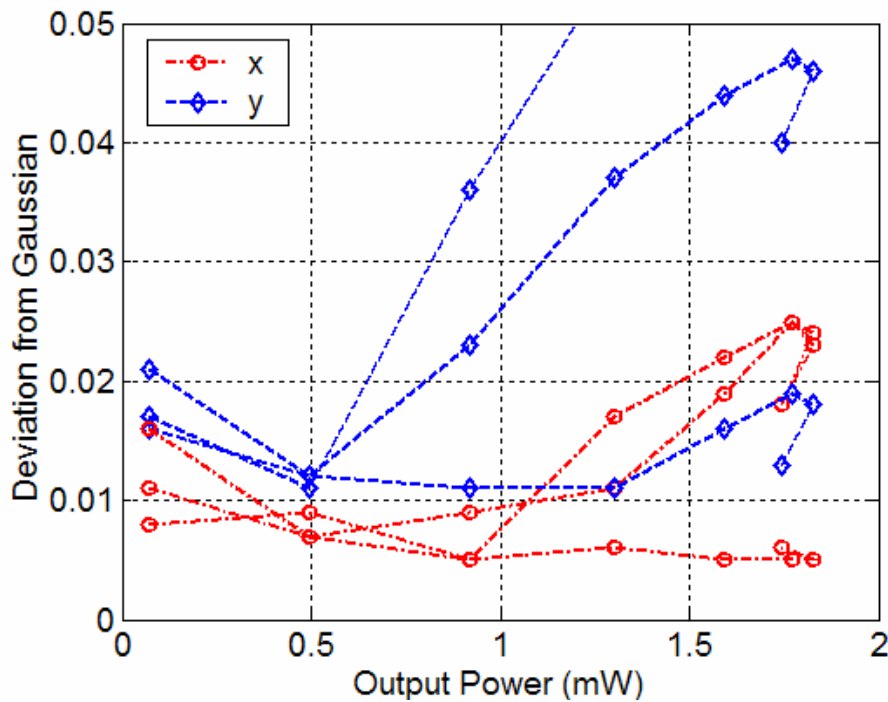
- Displace oxide layer in P-DBR
- Reduced index confinement
- Increased scattering loss
- High order mode suppression



*Hadley, JQE, v32, n4, p607, 1996.

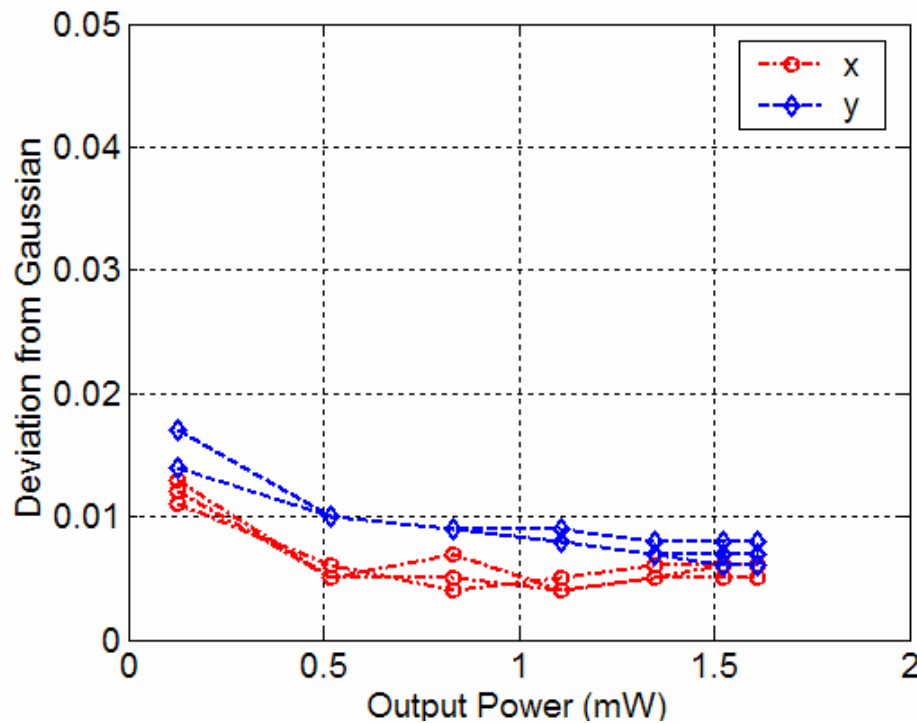
Mode Control Results

- 8th period oxide
- 7 μ m aperture

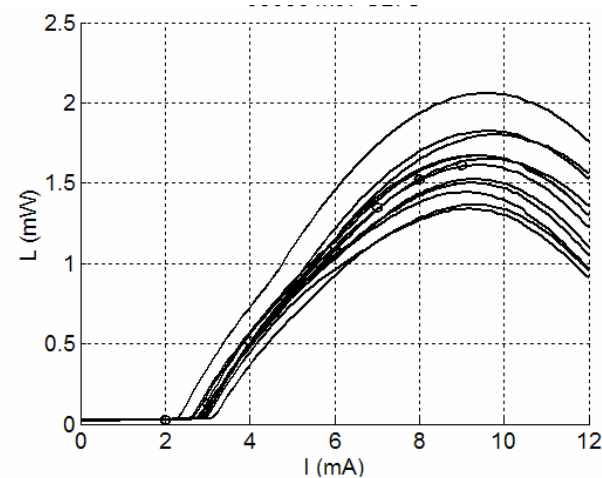
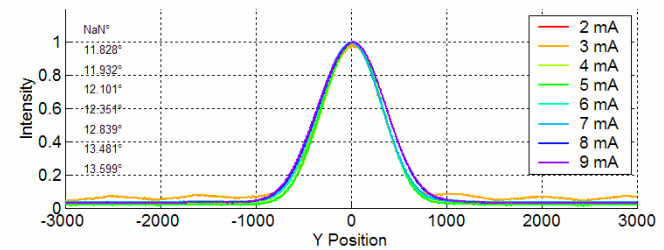
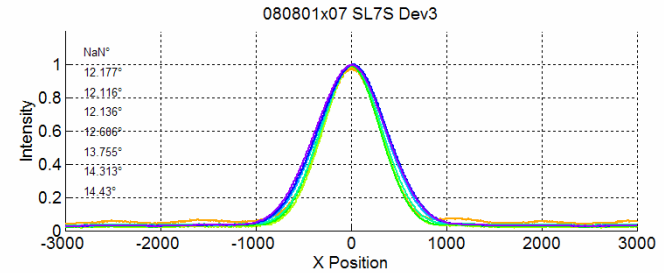


Mode Control Results

- 12th period oxide
- 7 μ m aperture



- Excessive current leakage

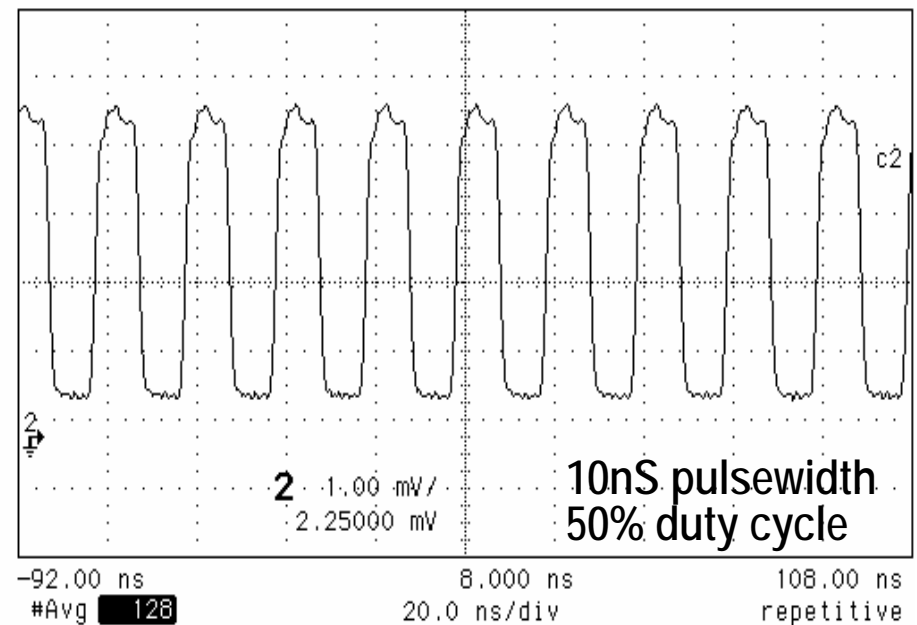
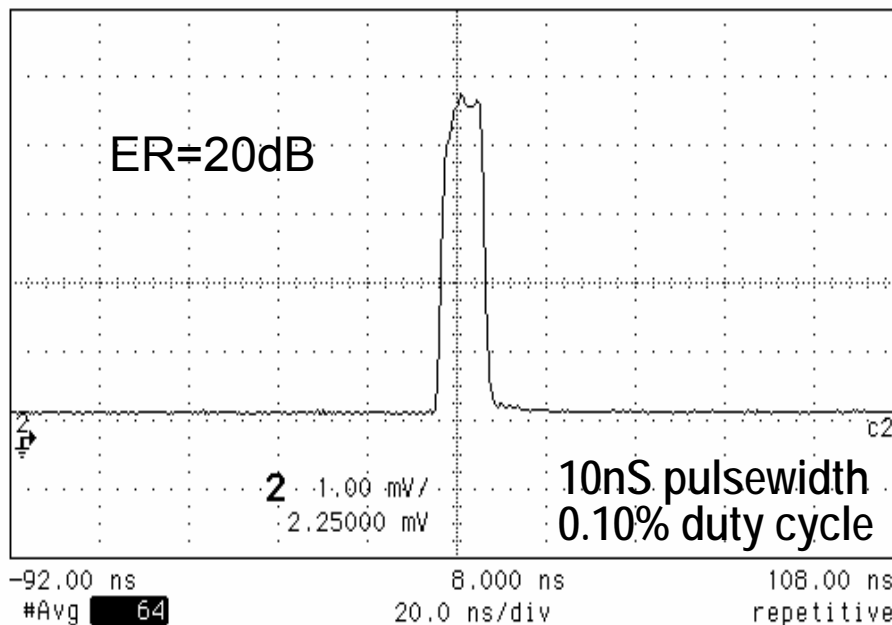


DCD Results

Duty Cycle Distortion

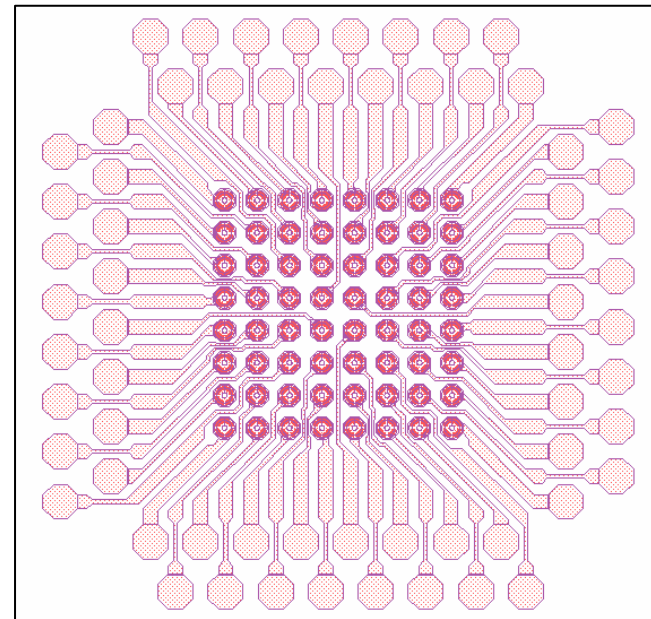
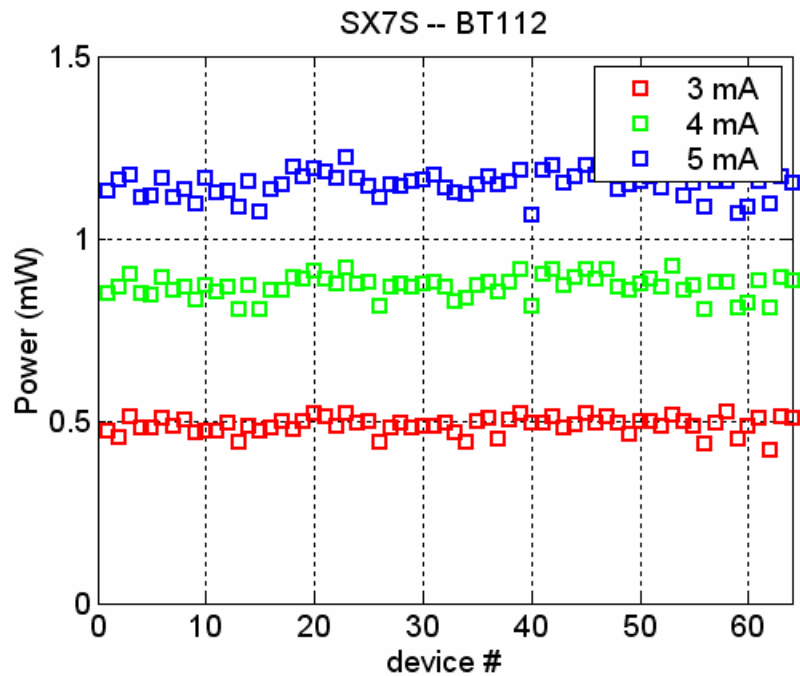
- DCD is a dependence of peak pulse power on duty cycle
- Proton VCSELs have issues with DCD due to thermal effects

12th period oxide



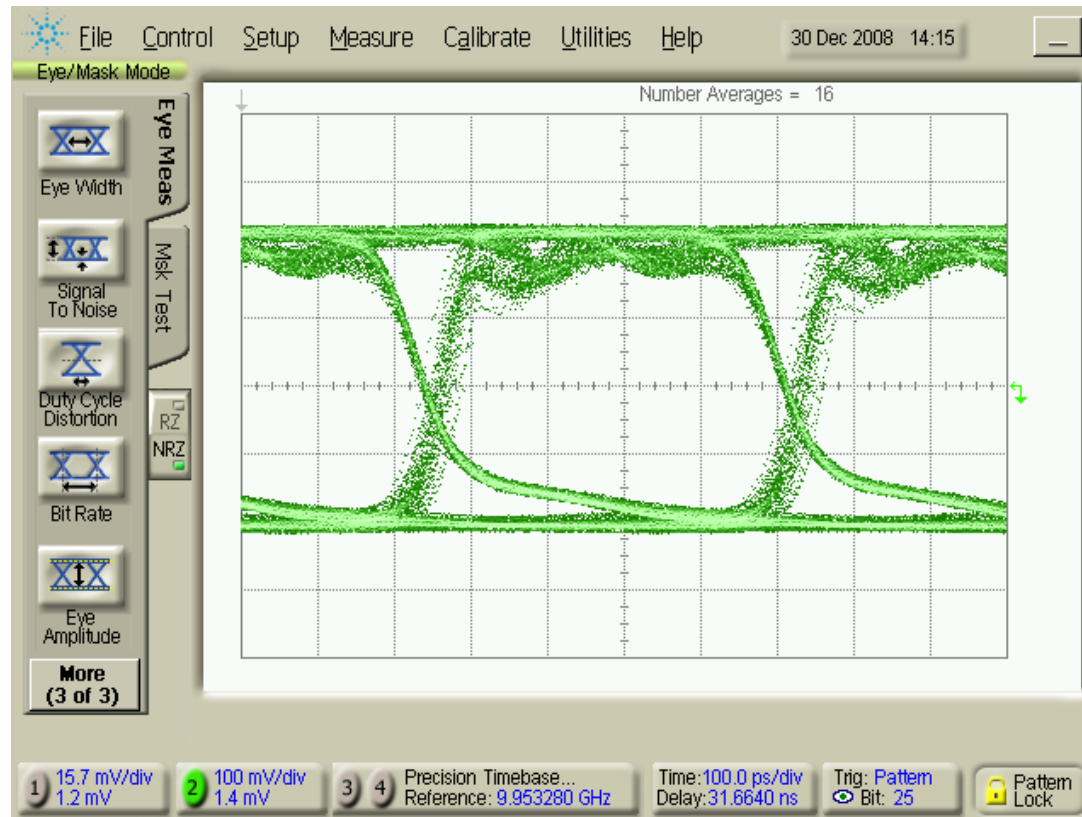
Uniformity

- 670nm oxide VCSEL 8x8 array uniformity
- 12th period oxide



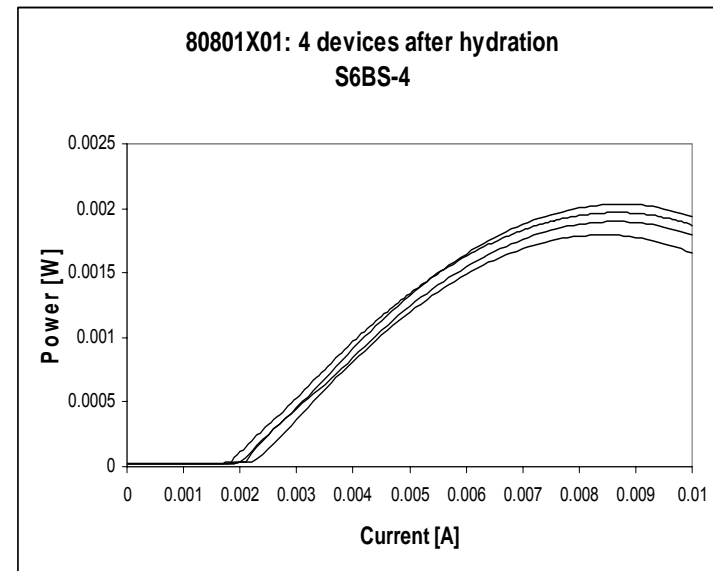
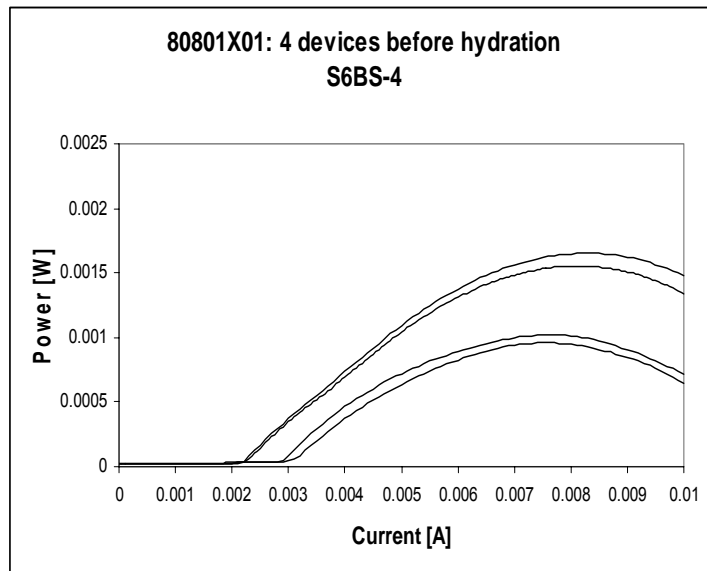
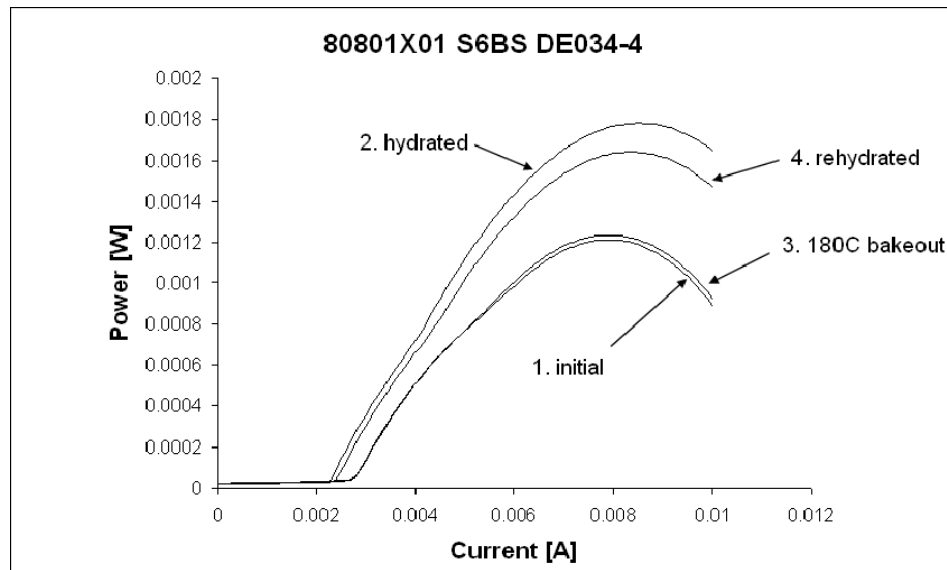
High Speed Modulation

- 2.125GB/s PRBS 2⁷
- ~10dB ER



670nm Unfiltered Eye @ 2.125G

Nitride Hydration Surprise



Summary

- Investigated multiple thermal management techniques
 - Surface and lateral mesa heatsinking promising
 - Substrate removal cost/benefit not compelling
 - Improved DBR design is highly effective
 - Direct heatsinking of active region inconclusive
- Raised oxide highly effective for mode control
 - 2mW, 7 μ m aperture, full operating range
 - Minimal DCD
 - Need to reduce leakage